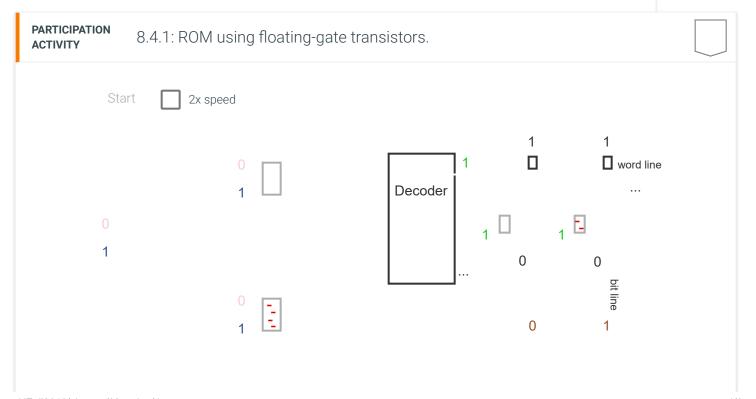
1/3/2019 8.4. ROM design

## 8.4 ROM design

## **ROM using floating-gate transistors**

Flip-flops, SRAMs, and DRAMs lose stored bits when electrical power is removed (*volatile* memory). In contrast, **ROM** (readretains stored bits when power is removed (*non-volatile* memory), by using technology that usually has slow writes, so write frequent than reads; hence the term "read-only" (a misnomer when writing is in fact possible). Writing to a ROM is called **pr** ROM.

Bit storage in a ROM commonly uses a *floating-gate transistor* having a special region where electrons can be trapped, sta without power. Applying a large positive voltage traps the electrons (programming). A large negative voltage frees the elect Applying such large voltages long enough to trap or free electrons is slow, which is why writing a ROM is slow.



| Natar The character of | " : ":f - DOI         | 1                   | alaatuiaal faatuusa laa | ومروم والمشرو ومرون والمال والمرون |
|------------------------|-----------------------|---------------------|-------------------------|------------------------------------|
| Note: The above is a   | logical view of a RUI | /i, oversimpiliying | electrical reatures be  | yond this material's scope.        |

| PARTICIPATION<br>ACTIVITY | 8.4.2: ROM using floating-gate transistors.                   |  |
|---------------------------|---|--|
|                           | rammed floating-gate<br>(no electrons trapped in the<br>ite)  |  |
| O acts                    | as a normal transistor  |  |
| O acts                    | opposite a normal transistor.                                 |  |
| O won                     | 't conduct  |  |
| , ,                       | med floating-gate transistor<br>trapped in the floating gate) |  |
| O acts                    | as a normal transistor  |  |
| O acts                    | opposite a normal transistor.                                 |  |
| O won                     | 't conduct  |  |
|                           | ning a floating-gate transistor<br>a a large                  |  |
| O posi                    | tive voltage  |  |
| O nega                    | ative voltage   |  |
| O ham                     | nmer  |  |
|                           | Ploating-gate transistor is large                             |  |

| opositive voltage   |  |
|---|--|
| O negative voltage  |  |
| 5) A 256x16 ROM would have how many word lines?  O 8 O 16   |  |
| <ul><li>O 256</li><li>6) A 256x16 ROM would have how many floating-gate transistors?</li><li>O 16</li></ul>   |  |
| <ul><li>256</li><li>4096</li></ul>  |  |
| 7) A ROM has 8 bits per location. Location 99 has only the first two transistors programmed (electrons trapped). What value is stored at location 99? |  |
| O 11000000  |  |
| O 00111111  |  |
| O 11111111  |  |
| 8) The ROM shown above would use to achieve the 1's and 0's at the data output.   |  |
| O normal logic  |  |
| O special circuitry   |  |

8.4. ROM design

## **ROM types**

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Numerous ROM types exist.

- Mask-programmed ROM: The word line to bit line connections are hardwired during chip manufacturing, and can nev
- **OTP ROM** (one-time programmable ROM): The word line to bit line connections have a fuse that can be "blown" to bre connection. A user can program the device only once.
- **EPROM** (erasable programmable ROM): Programming uses large positive voltage to trap electrons in a floating-gate t erasing is done by placing the chip under ultraviolet light to provide the energy to free the trapped electrons. This RON the more convenient EEPROM.
- **EEPROM** (electrically-erasable programmable ROM): Programming uses large positive voltage to trap electrons in a fl transistor, and erasing uses a large negative voltage.
- **Flash**: Programming uses large positive voltage to trap electrons in a floating-gate transistor, and erasing uses a large voltage to quickly erase entire blocks of locations at one time, like a "flash".

| PARTICIPATION 8.4.3: ROM type: | S.                              |                      |                                      |
|--------------------------------|---------------------------------|----------------------|--------------------------------------|
| Start 2x speed                 |                                 |                      |                                      |
| Mask-programmed<br>ROM         | Programmed during manufacturing | word lin<br>bit line | е                                    |
| OTP ROM                        |                                 |                      | Programming<br>blows<br>fuses        |
| EPROM                          |                                 | ~G, ~G,              | Entire chip<br>erased by UV light    |
| EEPROM                         |                                 | ~G, ~G,              | Each word erased by negative voltage |
|                                |                                 | ^c, *e,              | Entire blocks quickly erased by      |

8.4. ROM design

Flash

negative voltage

PARTICIPATION ACTIVITY

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8.4.4: ROM types.

Match the ROM type with the most likely usage scenario.

**EPROM** 

Mask-programmed ROM

Flash

OTP ROM

**EEPROM** 

Storing program instructions in a calculator that will be produced in the hundreds of millions.

Storing a unique ID number for a secure card key, which should never be changed.

Storing a program in a microprocessor chip being used for prototyping in an engineering lab, with the chip being reprogrammed a few times a day, in the 1980s.

Storing 256 phone numbers in a portable keychain device, each number reprogrammable by some button clicks.

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A digital photo frame to which 8 photos can be uploaded, with the frame showing a different photo every minute.

Reset

## Exploring further:

- ROM (Wikipedia)
- Flash (Wikipedia)
- Provide feedback on this section